

N-Ch 60V Fast Switching MOSFETs

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

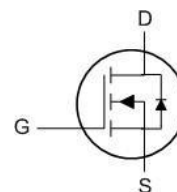
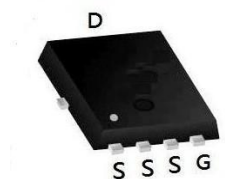
- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Product Summary



BVDSS	RDSON	ID
60V	2.4mΩ	125A

PDFN5060-8L Pin Configuration



Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		60	V
I_D	Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	125	A
	Continuous Drain Current	$T_C = 100\text{ }^{\circ}\text{C}$	101	A
I_{DM}^{a1}	Pulsed Drain Current		641	A
E_{AS}^{a2}	Single pulse avalanche energy		189	mJ
V_{GS}	Gate-to-Source Voltage		± 20	V
P_D	Power Dissipation		113	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering		260	$^{\circ}\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.11	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	39.4	$^{\circ}\text{C}/\text{W}$

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Electrical Characteristics (T_c = 25°C unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 60V, V _{GS} = 0V	--	--	1	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+20V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-20V	--	--	-100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250μA	1.2	--	2.2	V
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =20A	--	2.4	2.9	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 30V f = 1.0MHz	--	4610	6915	pF
C _{oss}	Output Capacitance		--	2188	3282	
C _{rss}	Reverse Transfer Capacitance		--	66	132	
R _g	Gate resistance		--	0.93	18.8	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =40A V _{DS} = 30V V _{GS} = 10V R _G = 2.7Ω	--	14.13	--	ns
t _r	Rise Time		--	63.73	--	
t _{d(OFF)}	Turn-Off Delay Time		--	46.8	--	
t _f	Fall Time		--	105.07	--	
Q _g	Total Gate Charge	V _{GS} =10V V _{DS} = 30V I _D =40A	--	74.37	111.56	nC
Q _{gs}	Gate Source Charge		--	17.26	--	
Q _{gd}	Gate Drain Charge		--	9.44	18.88	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I _S	Diode Forward Current	T _C =25 °C	--	--	125	A
V _{SD}	Diode Forward Voltage	I _S =40A, V _{GS} =0V	--	0.83	1.2	V
t _{rr}	Reverse Recovery time	I _S =40A, dI/dt=300A/μs	--	52.78	105.56	ns
Q _{rr}	Reverse Recovery Charge		--	56.31	112.62	nC

a¹: Repetitive rating; pulse width limited by maximum junction temperature a²:
V_{DD}=30V, L=0.3mH, R_g=25Ω, Starting T_J=25 °C

Typical Performance Characteristics

Fig 1: Output Characteristics

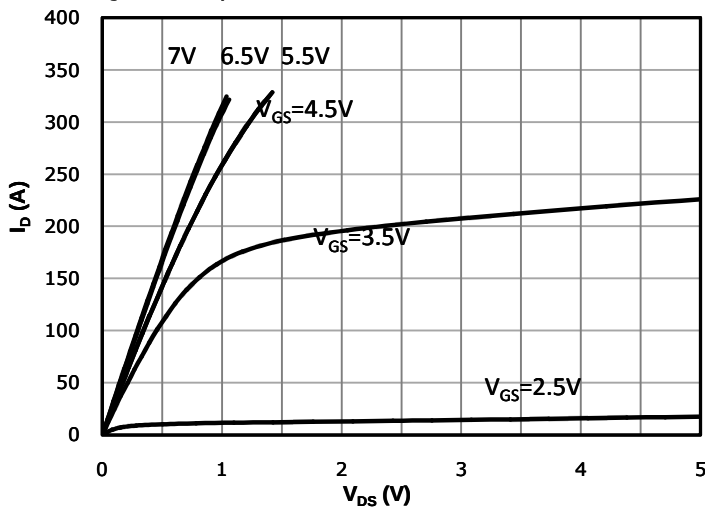


Fig 2: Transfer Characteristics

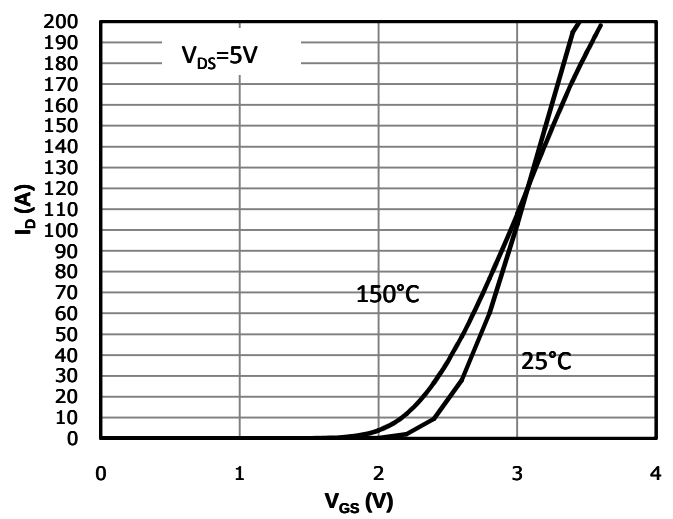


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

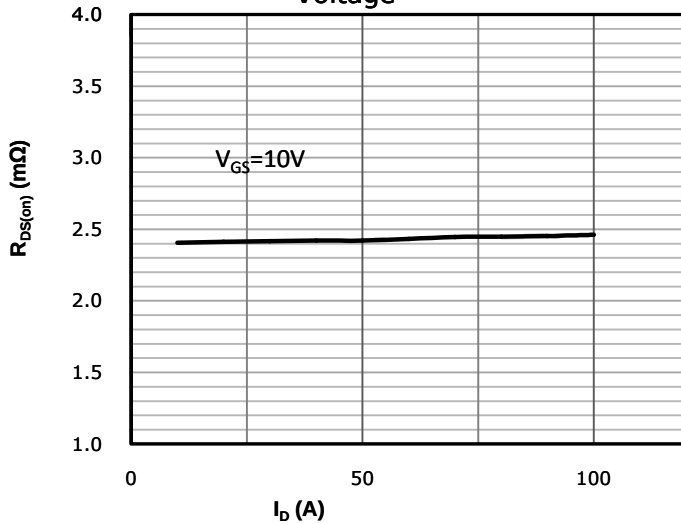


Fig 4: $R_{DS(on)}$ vs Gate Voltage

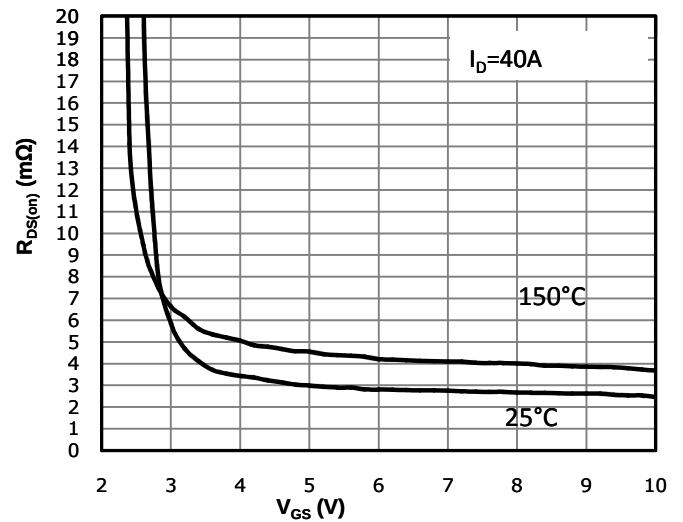


Fig 5: $R_{DS(on)}$ vs. Temperature

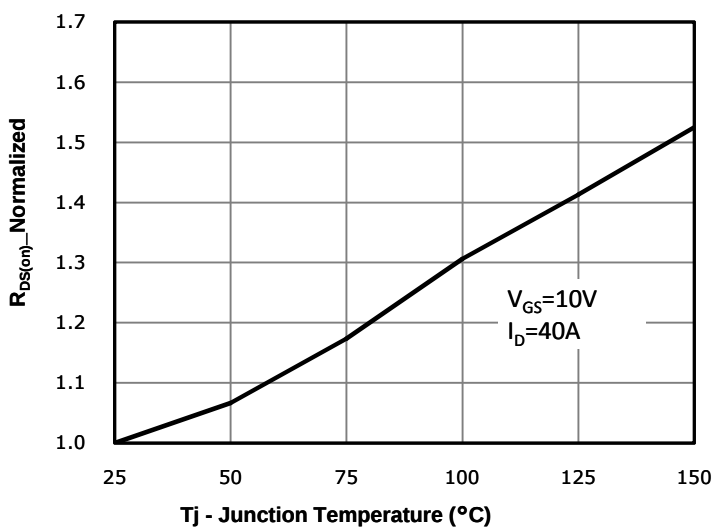
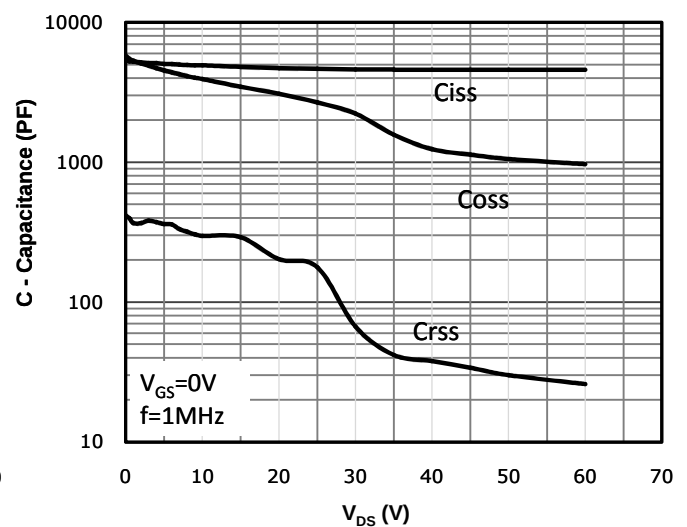


Fig 6: Capacitance Characteristics



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Fig 7: Gate Charge Characteristics

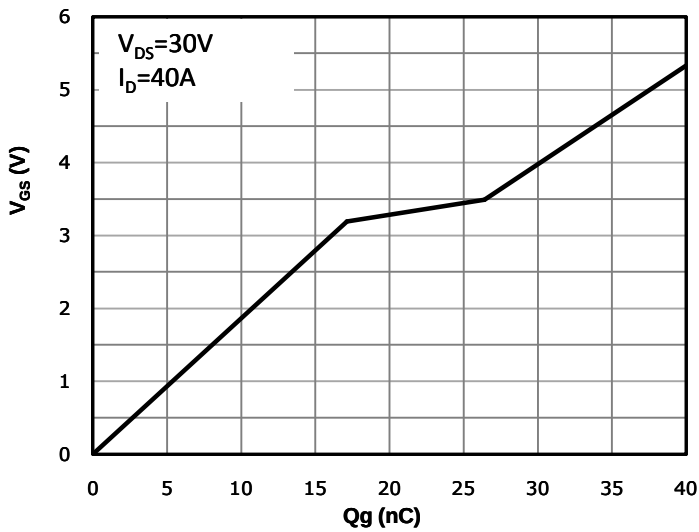


Fig 8: Body-diode Forward Characteristics

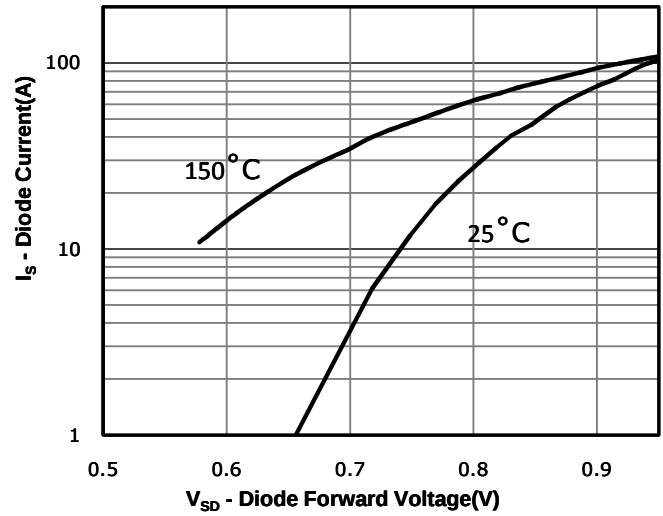


Fig 9: Power Dissipation

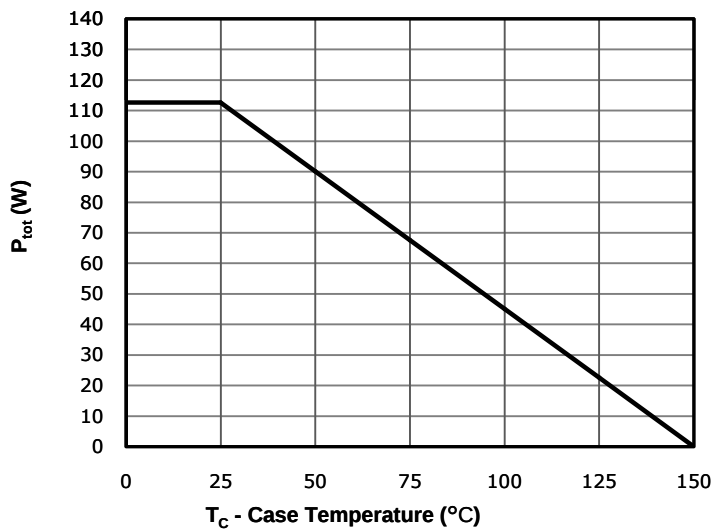


Fig 10: Drain Current Derating

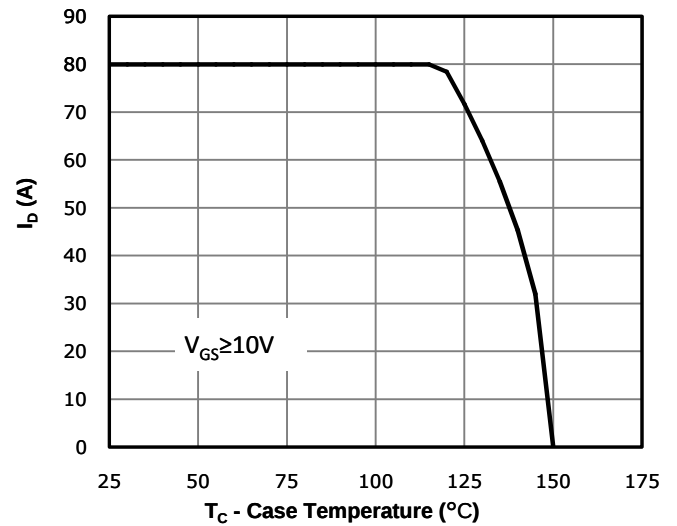


Fig 11: Safe Operating Area

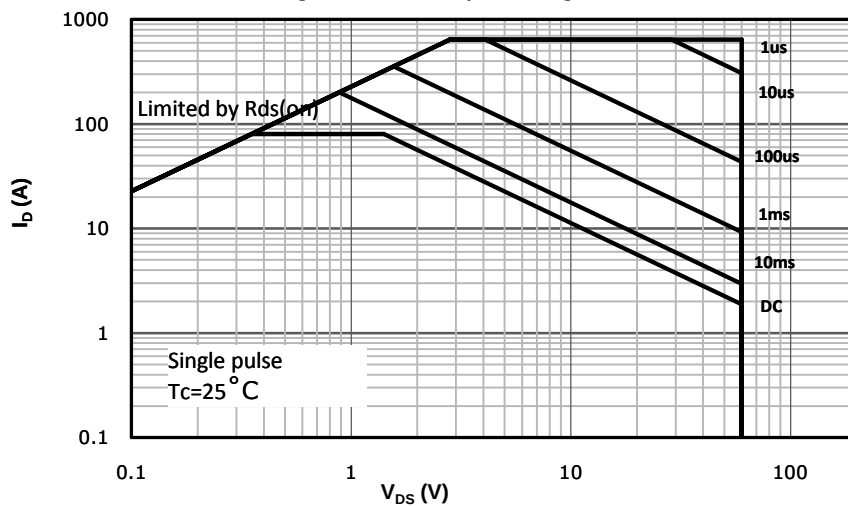
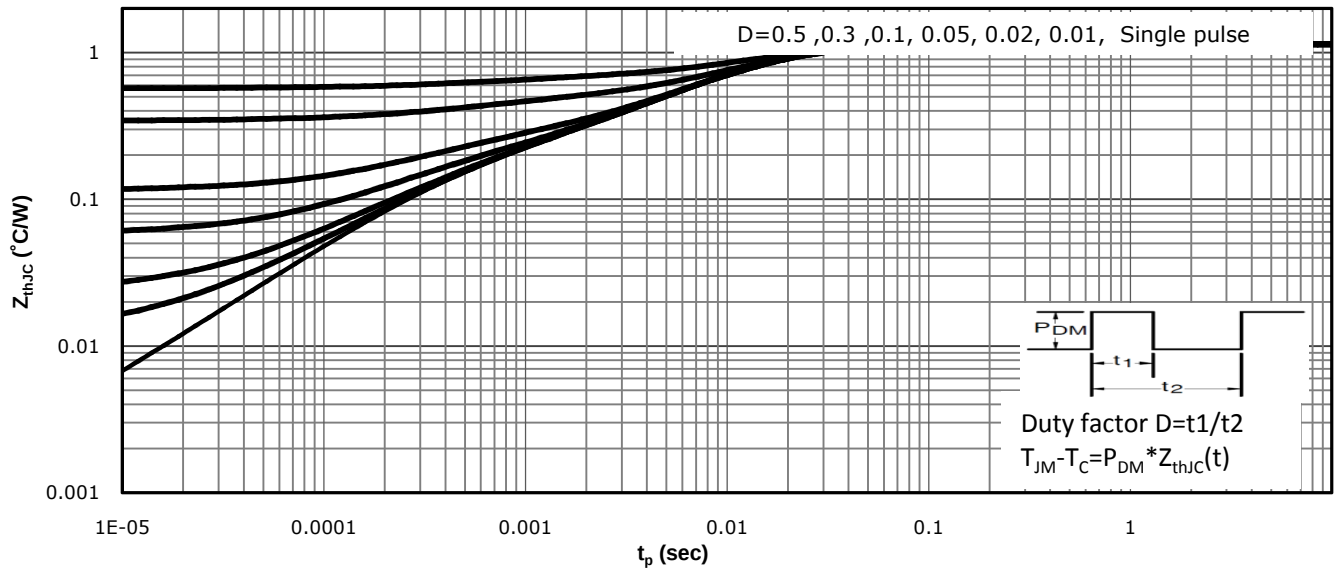
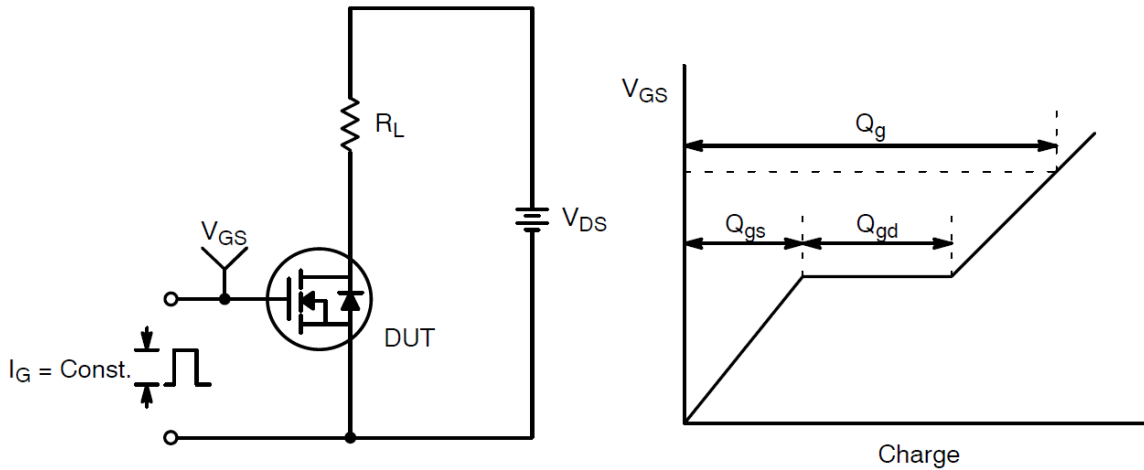




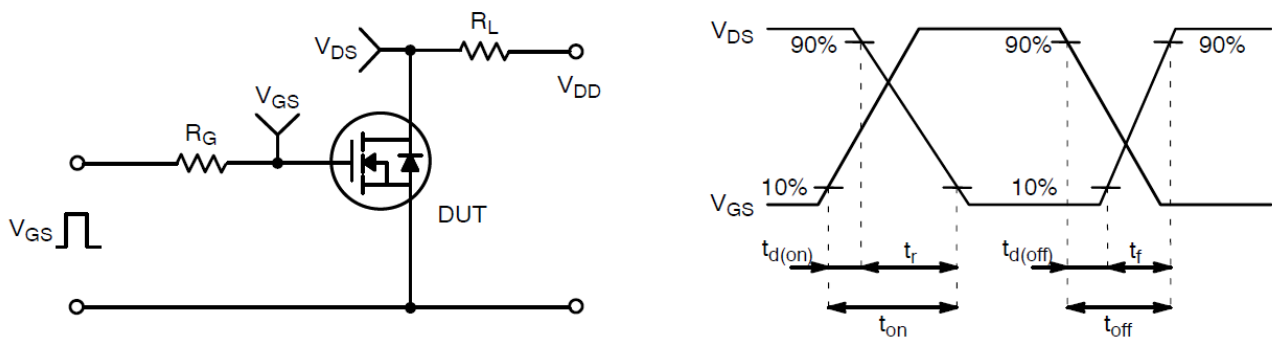
Fig 12: Max. Transient Thermal Impedance



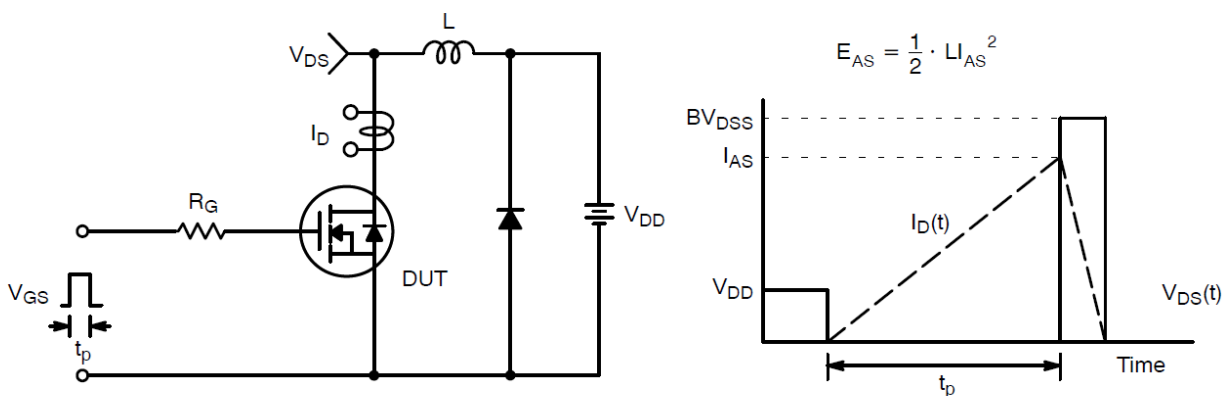
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform

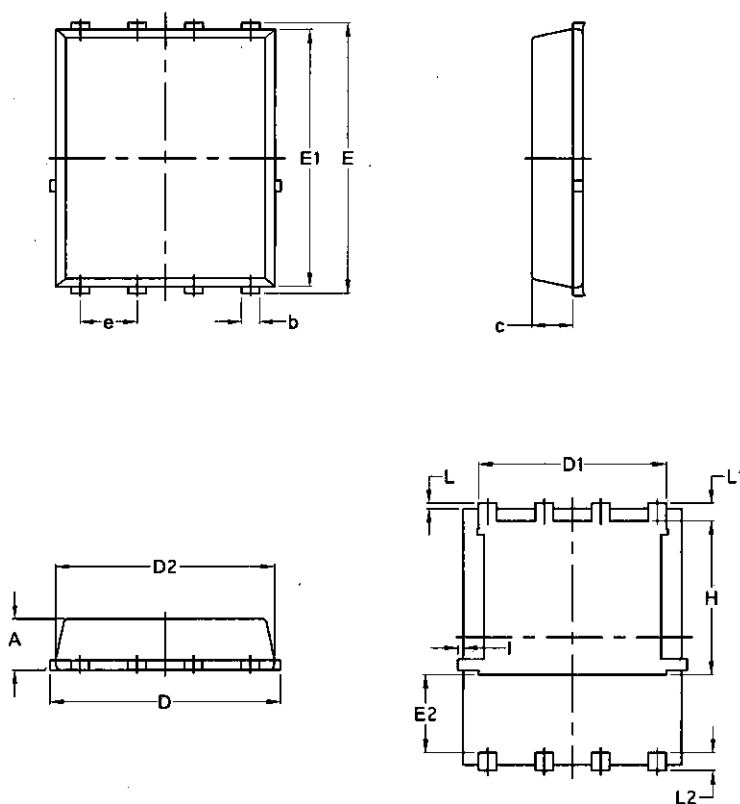


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-PDFN5060-8L-Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070